

/ Descriptions

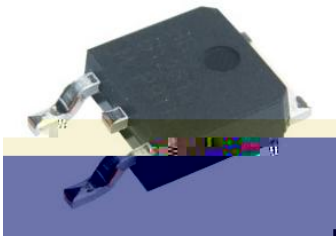
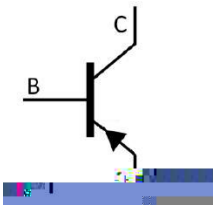
KF \$,) GE G Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

D 9

High breakdown voltage, adoption of MBIT process excellent h_{FE} linearity

High voltage driver applications.

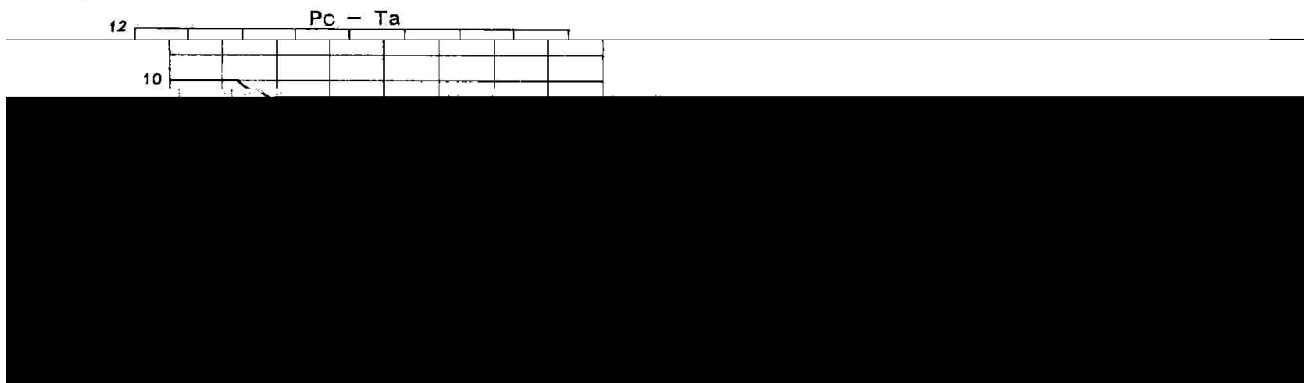
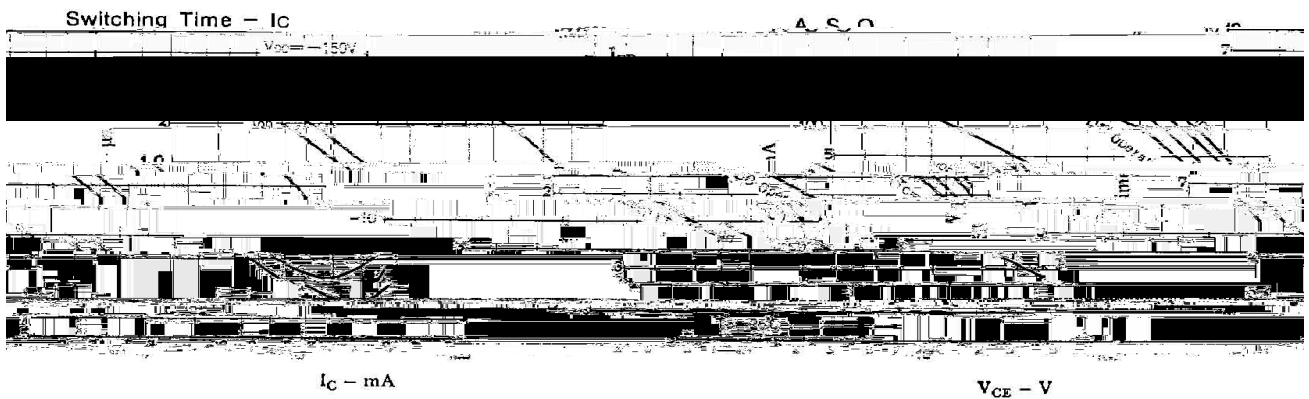
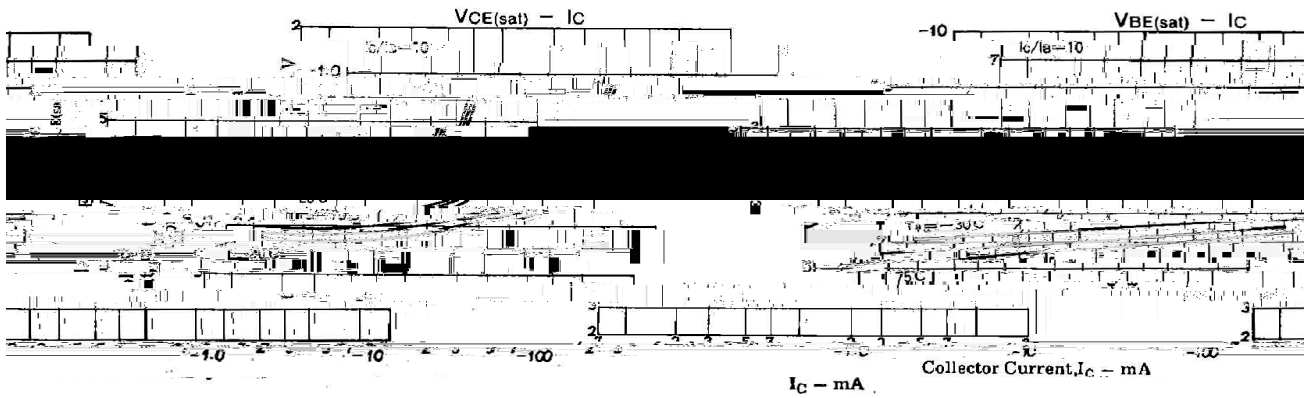
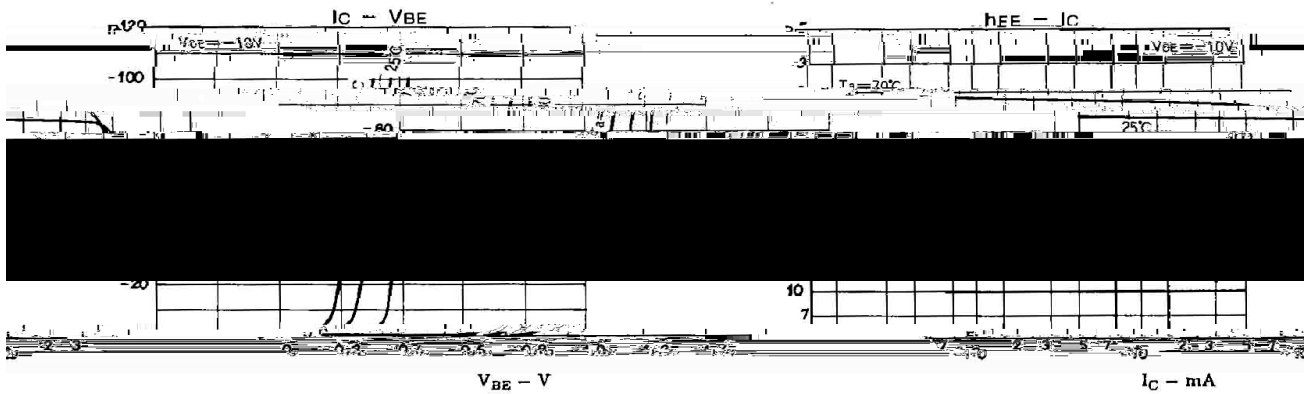


PIN1 Base PIN 2,4 Collector PIN 3 Emitter

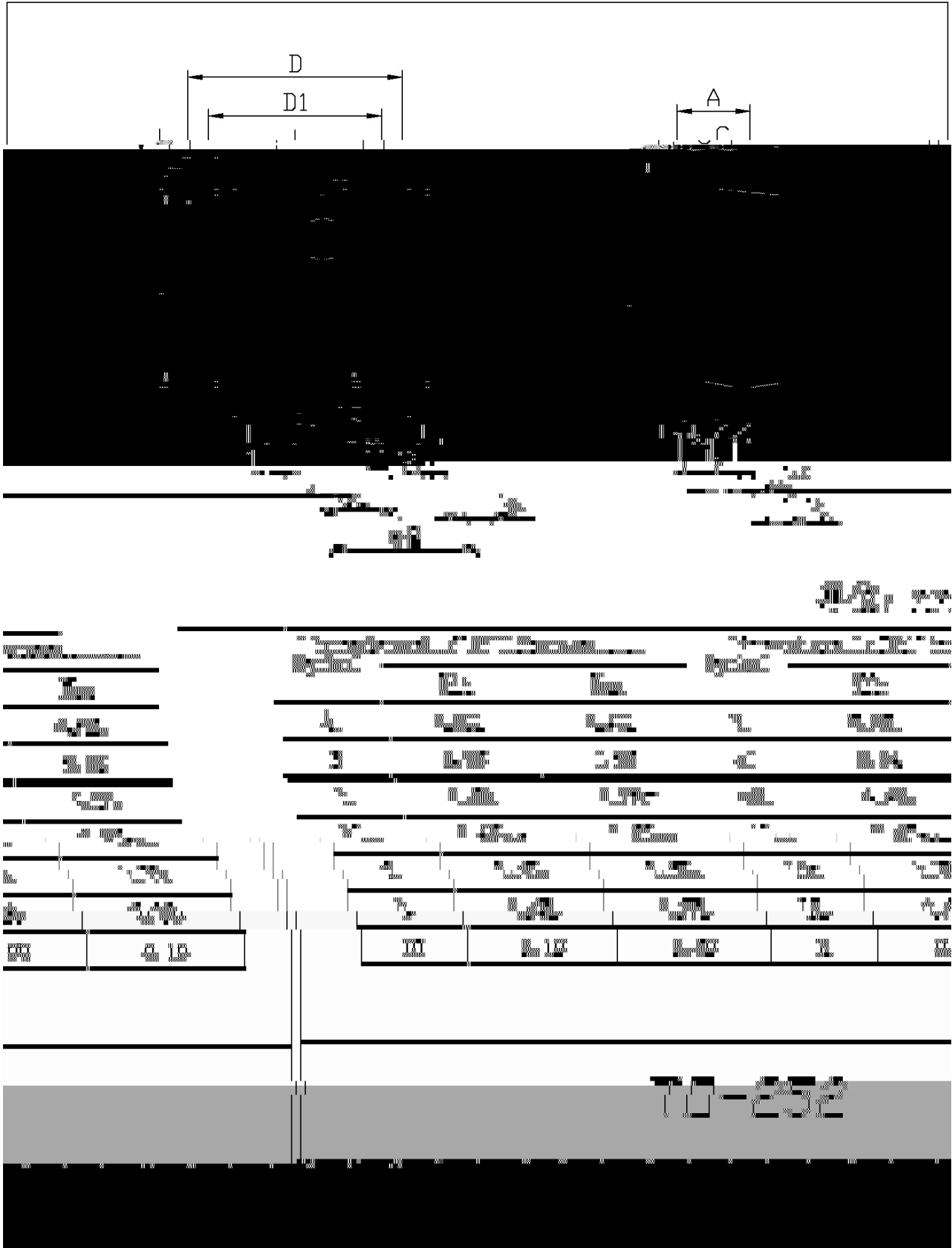
/ h_{FE} Classifications & Marking

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-400	V

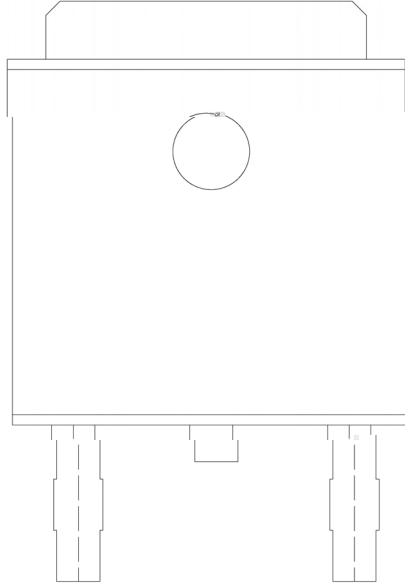
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

A1700

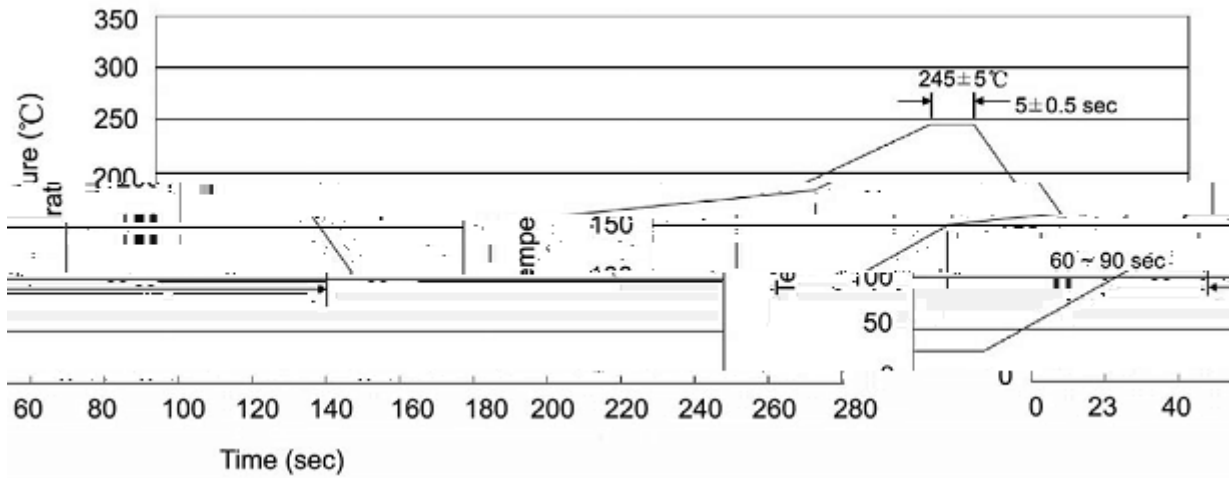
D1 h_{FE}

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Note:

BR: A13()TjZmparyWFO

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|------------|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245..5 | | 5..0.5sec; | | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260..5 10..1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units	Dimension	(unit mm ³)
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